NSR0170HT1G

Schottky Barrier Diode

Schottky barrier diodes are optimized for very low forward voltage drop and low leakage current and are used in a wide range of dc–dc converter, clamping and protection applications in portable devices. NSR0170H in a SOD–323 small footprint package enables designers to meet the challenging task of achieving higher efficiency designs and meeting reduced board space requirements.

Features

- Very Low Forward Voltage Drop 560 mV @ 10 mA
- Low Reverse Current 25 nA @ 50 V V_R
- 70 mA of Continuous Forward Current
- Power Dissipation of 180 mW with Minimum Trace
- Very High Switching Speed
- Low Capacitance -CT = 2 pF
- NSVR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Automotive Modules
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	70	V
Forward Current (DC)	١ _F	70	mA
Non–Repetitive Peak Surge Forward Current	I _{FSM}	100	mA
ESD Rating: Human Body Model Machine Model	ESD	Class 2 Class M3	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

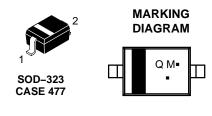


ON Semiconductor®

http://onsemi.com

70 V SCHOTTKY BARRIER DIODE





Q = Specific Device Code

M = Month Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSR0170HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
NSVR0170HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ $T_A = 25^{\circ}C$	R _{θJA} P _D			680 180	°C/W mW
Thermal Resistance Junction–to–Ambient (Note 2) Total Power Dissipation @ $T_A = 25^{\circ}C$	R _{θJA} P _D			440 280	°C/W mW
Junction and Storage Temperature Range	T _J , T _{stg}			-55 to +150	°C

Mounted onto a 4 in square FR-4 board 10 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
 Mounted onto a 4 in square FR-4 board 1 in sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage $(V_R = 50 V)$ $(V_R = 70 V)$	I _R		25 -	90 3.0	nA μA
Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 15 \text{ mA})$	V _F		340 560 650	390 640 730	mV
Total Capacitance ($V_R = 0 V, f = 1 MHz$)	СТ		2.0		pF

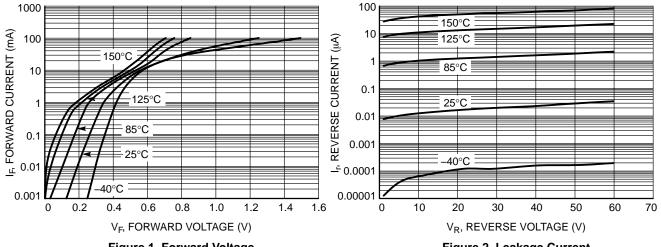
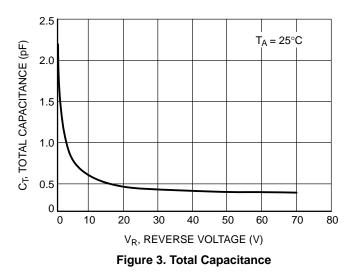




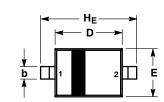
Figure 2. Leakage Current

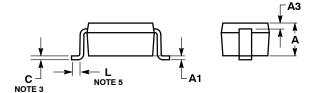




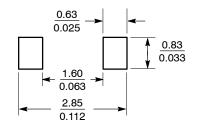








SOLDERING FOOTPRINT*



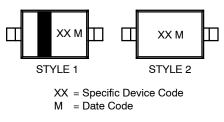
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 13 MAR 2007

- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
Е	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

GENERIC **MARKING DIAGRAM***



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE STYLE 2: NO POLARITY

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SOD-323 CASE 477-02

ISSUE H

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